

Abstract of the Disclosure

An ion implanting apparatus includes an analyzer unit for analyzing ions to be implanted into a wafer from among those ions in a beam produced by an ionization unit, a vacuum unit for producing a vacuum in the analyzer unit, a vacuum gauge for measuring the pressure inside the analyzer unit, and a shield for preventing a magnetic field employed by the analyzer unit from affecting the vacuum gauge. The shield has a plurality of magnetic field shielding plates encircling the vacuum gauge and dielectric material inserted between the magnetic shielding plates. The shield prevents the vacuum gauge from being influenced by the magnetic field generated by the analyzer unit. Therefore, the vacuum level inside the analyzer unit can be precisely measured.